

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

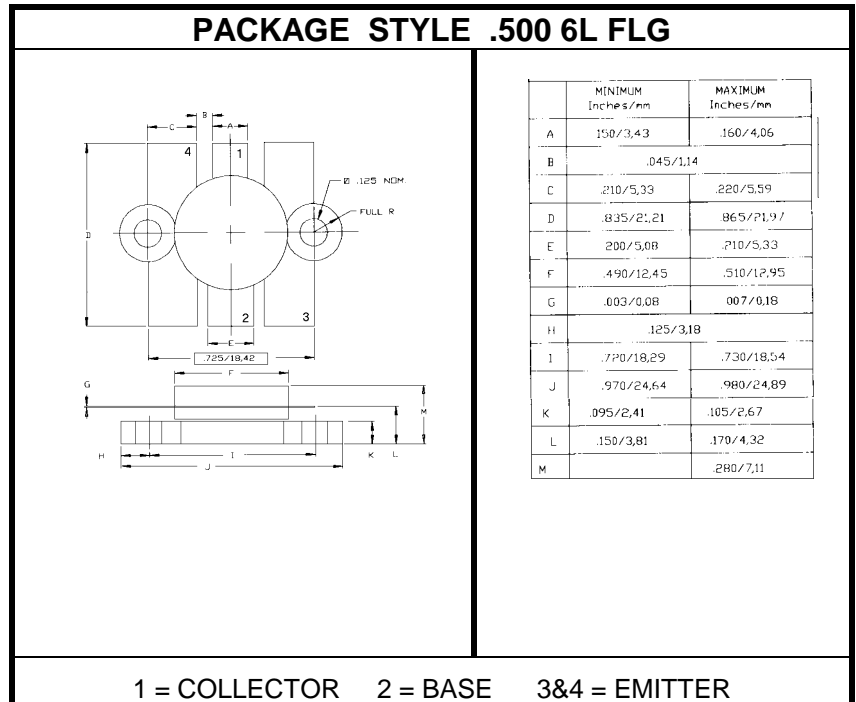
The **ASI BM100-28** is Designed for high power VHF Applications up to 200 MHz.

FEATURES:

- Common Emitter
- $P_G = 8.5$ dB at 20 W/175 MHz
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	20 A
V_{CEO}	33 V
V_{CES}	65 V
V_{EBO}	4.0 V
P_{DISS}	270 W @ $T_C = 25^\circ C$
T_J	$-65^\circ C$ to $+200^\circ C$
T_{STG}	$-65^\circ C$ to $+150^\circ C$
θ_{JC}	$0.65^\circ C/W$


CHARACTERISTICS $T_C = 25^\circ C$

SYMBOL	TEST CONDITIONS			MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	$I_C = 50$ mA			33			V
BV_{CES}	$I_C = 100$ mA			65			V
BV_{EBO}	$I_E = 5.0$ mA			4.0			V
h_{FE}	$V_{CE} = 5.0$ V	$I_C = 1.0$ A		10			---
C_{CB}	$V_{VB} = 28$ V	$f = 1.0$ MHz			200		pF
P_G η_C	$V_{CC} = 28$ V	$P_{OUT} = 100$ W	$f = 175$ MHz	8.5	60		dB %